

Appl. No. 09/817,967

Amdt. dated January 20, 2005

Reply to Office action of January 14, 2005

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-10 (canceled).

Claim 11 (currently amended). A component, which comprises:

a substrate;

a lower insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  and having a region;

at least one upper insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$ , being chemically different from said lower insulating layer, and having a region; and

at least one activated region that is selectively activated using an activator selected from the group consisting of a gas, a liquid, a solution, and plasma;

said at least one activated region being selected from the group consisting of said region of said lower insulating layer and said region of said at least one upper insulating layer,

Appl. No. 09/817,967

Amdt. dated January 20, 2005

Reply to Office action of January 14, 2005

said activated region therefore being an activated insulating layer;

said lower insulation layer located adjacent said at least one upper insulation layer;

said activated region being one of a selectively modified region and a surface of said activated insulating layer such that subsequently only said activated region can be subjected to a process selected from a group of metallization, photosensitization, and hydrophobicization.

Claim 12 (previously presented). The component according to claim 11, wherein said substrate, said lower insulating layer, and said at least one upper insulating layer form a component selected from the group consisting of an electronic component and a microelectronic component.

Claim 13 (canceled).

Claim 14 (previously presented). The component according to claim 11, wherein said at least one said upper layer is a layer selected from the group consisting of a patterned layer and a mask layer for activating said lower layer.

Appl. No. 09/817,967

Amdt. dated January 20, 2005

Reply to Office action of January 14, 2005

Claim 15 (previously presented). The component according to claim 11, wherein said at least one activated region is a region selected from the group consisting of a seeded region and a metallized region.

Claims 16-23 (canceled).

Claim 24 (previously presented). A process for producing a component, which comprises:

in a first working step, applying a lower insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  to a substrate;

in a second working step, selectively activating at least one region of the lower insulating layer using an activator selected from the group consisting of a gas, a liquid, a solution and plasma for forming an activated region being one of a selectively modified region and a surface of the lower insulating layer; and

in a third working step, applying at least one upper insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  and being chemically different from said at least one

Appl. No. 09/817,967

Amdt. dated January 20, 2005

Reply to Office action of January 14, 2005

lower insulating layer to the lower, activated insulating layer and patterning the at least one upper insulating layer.

Claim 25 (previously presented). The process according to claim 24, which comprises patterning the lower insulating layer in the first working step.

Claim 26 (previously presented). The process according to claim 24, which comprises choosing a selected layer from the group consisting of the at least upper one insulating layer and the lower insulating layer and patterning the selected layer after the selected layer has been applied.

Claim 27 (previously presented). A process for producing a component, which comprises:

in a first working step, applying a first insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  to a substrate;

in a second working step, applying a second insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  and being chemically different from said at least one lower insulating layer and patterning the second insulating layer; and

Appl. No. 09/817,967

Amdt. dated January 20, 2005

Reply to Office action of January 14, 2005

in a third working step, selectively activating a layer selected from the group consisting of the first insulating layer and the second insulating layer using an activator selected from the group consisting of a gas, a liquid, a solution, and plasma for forming an activated insulating layer, the activating step includes the step of selectively modifying a region or a surface of the activated insulating layer.

Claim 28 (previously presented). The process according to claim 27, which comprises patterning the first insulating layer in the first working step.

Claim 29 (previously presented). The process according to claim 27, which comprises patterning the second insulating layer after the second working step and before the third working step.

Claim 30 (previously presented). The process according to claim 29, which comprises patterning the first insulating layer, after the first working step.

Claim 31 (previously presented). The process according to claim 27, which comprises patterning the first insulating layer, after the first working step.